

### Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \text{ max}}$	$I_D \text{ max}$ $T_C = +25^\circ\text{C}$
100V	28mΩ @ $V_{GS} = 10V$	55A

### Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

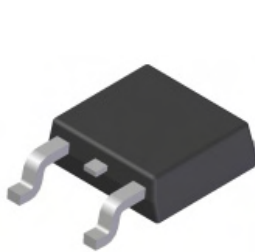
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

### Features

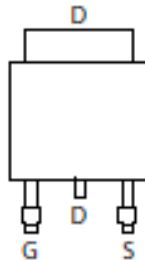
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low  $R_{DS(ON)}$  – Minimizes Power Losses
- Low  $Q_g$  – Minimizes Switching Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

### Mechanical Data

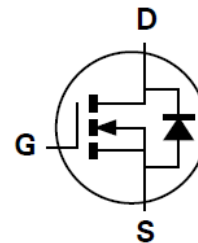
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



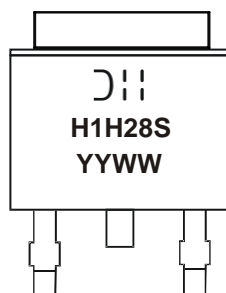
Equivalent Circuit

### Ordering Information (Note 5)

Part Number	Case	Packaging
DMNH10H028SK3Q-13	TO252	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_compliance\\_definitions/](http://www.diodes.com/quality/product_compliance_definitions/).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

### Marking Information



- D = Manufacturer's Marking
- H1H28S = Product Type Marking Code
- YYWW = Date Code Marking
- YY = Last Two Digits of Year (ex: 15 = 2015)
- WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	100	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>C</sub> = +25°C	55
		T <sub>C</sub> = +100°C	39
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	58	A
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	2.2	A
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	29	A
Avalanche Energy, L = 0.1mH	E <sub>AS</sub>	43	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	Steady State	74
		t < 10s	25
Total Power Dissipation (Note 7)	P <sub>D</sub>	3.7	W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>θJA</sub>	Steady State	40
		t < 10s	13
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	1.2	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current, T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2.0	2.5	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	20	28	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.0A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	2,245	—	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	173	—	pF	
Reverse Transfer Capacitance	C <sub>riss</sub>	—	68	—	pF	
Gate Resistance	R <sub>g</sub>	—	1.9	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	36	—	nC	V <sub>DS</sub> = 50V, I <sub>D</sub> = 20A
Total Gate Charge (V <sub>GS</sub> = 6V)	Q <sub>g</sub>	—	22	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	7.3	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	9.2	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	6.4	—	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 50V, R <sub>G</sub> = 3Ω, I <sub>D</sub> = 20A
Turn-On Rise Time	t <sub>r</sub>	—	5.8	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	17.8	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	4.8	—	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	35	—	ns	I <sub>F</sub> = 20A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	47	—	nC	I <sub>F</sub> = 20A, di/dt = 100A/μs

- Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to product testing.

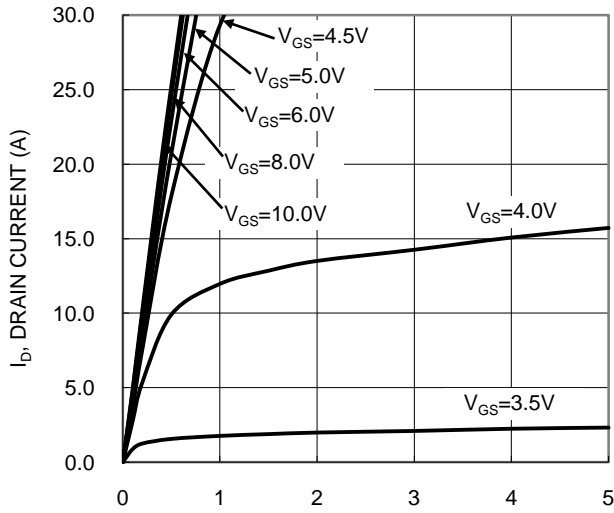


Figure 1. Typical Output Characteristic

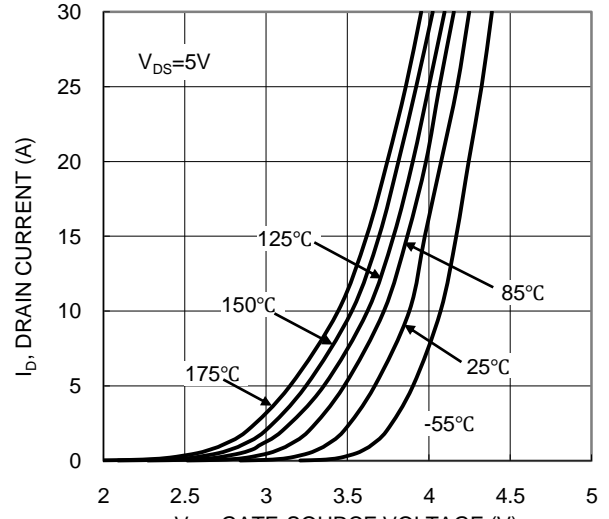


Figure 2. Typical Transfer Characteristic

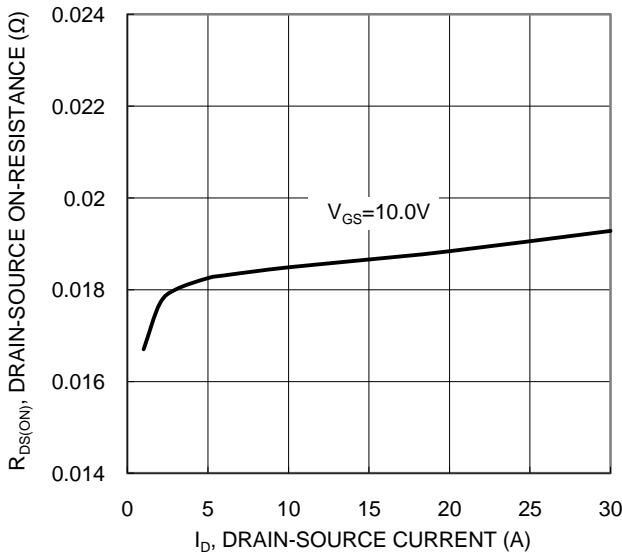


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

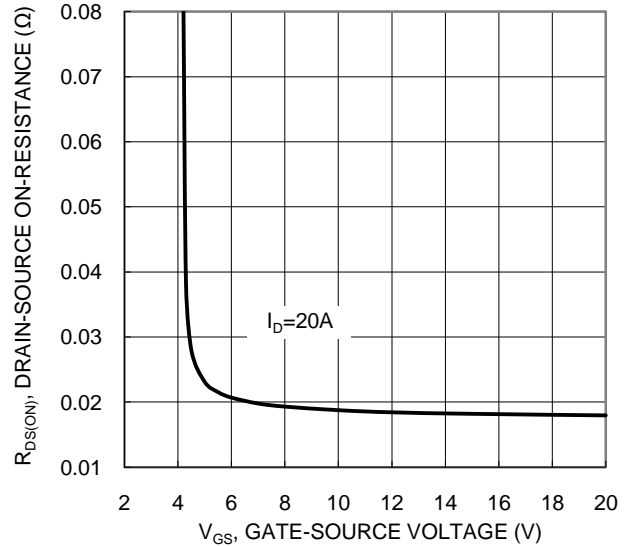


Figure 4. Typical Transfer Characteristic

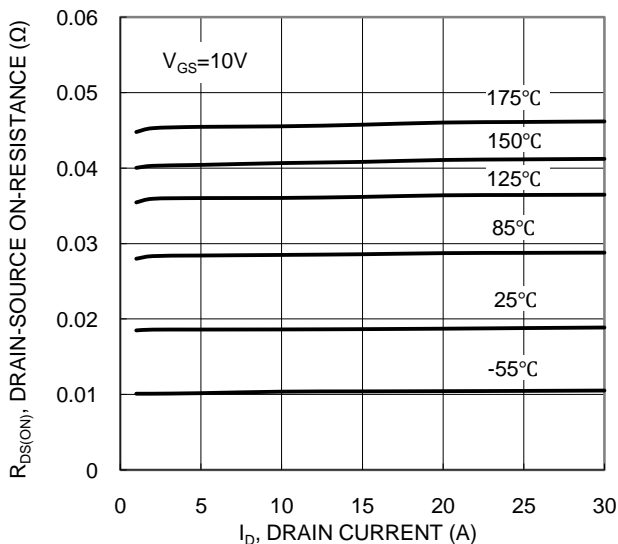


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

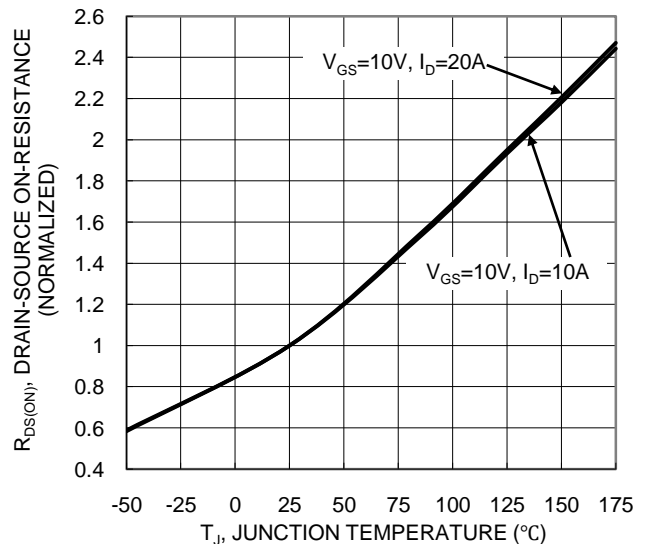


Figure 6. On-Resistance Variation with Temperature

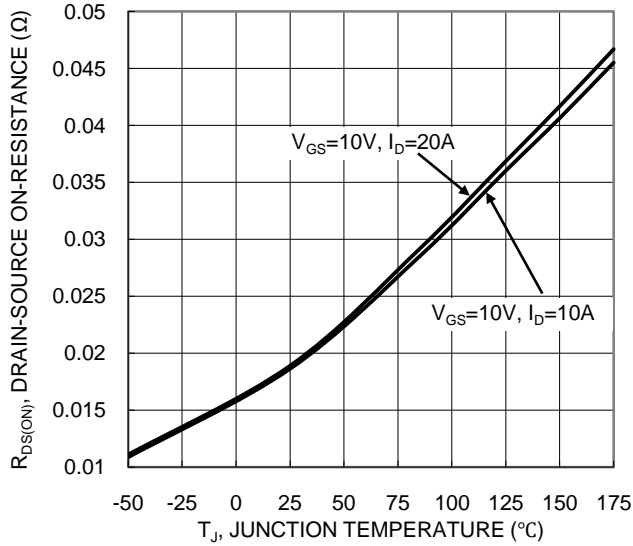


Figure 7. On-Resistance Variation with Temperature

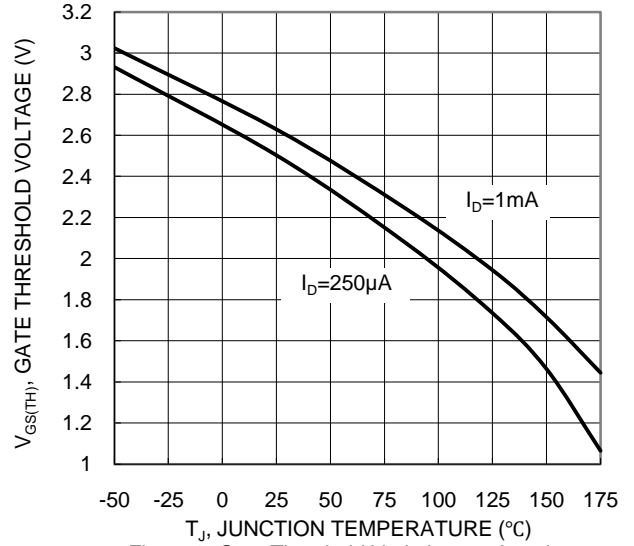


Figure 8. Gate Threshold Variation vs. Junction Temperature

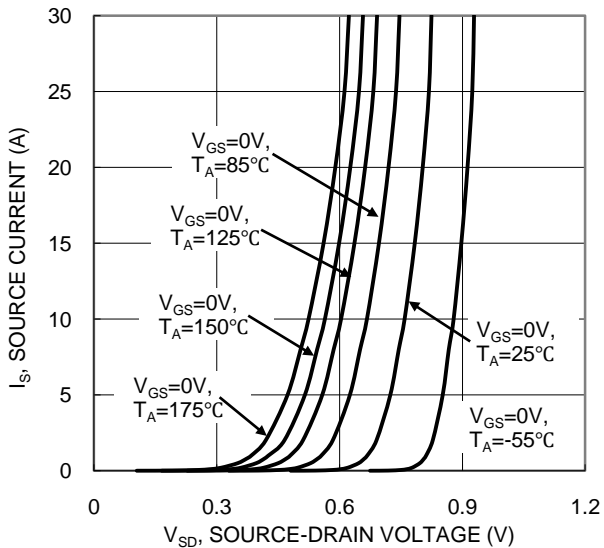


Figure 9. Diode Forward Voltage vs. Current

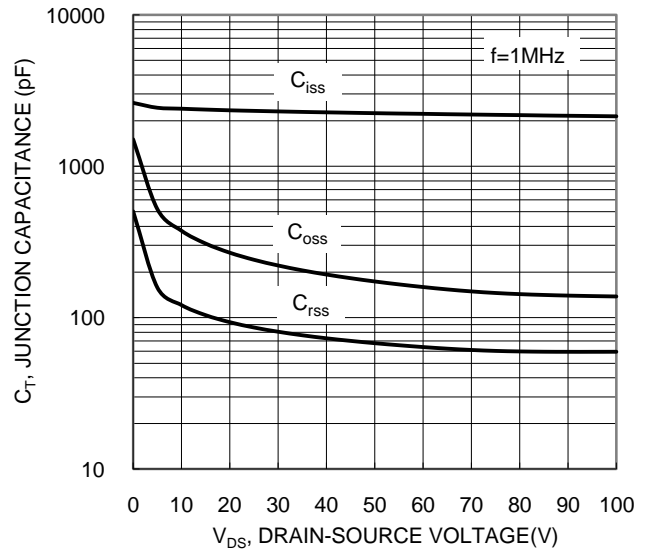


Figure 10. Typical Junction Capacitance

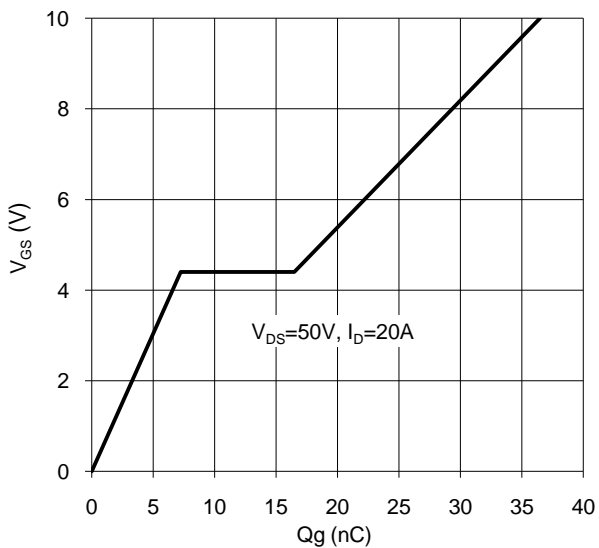


Figure 11. Gate Charge

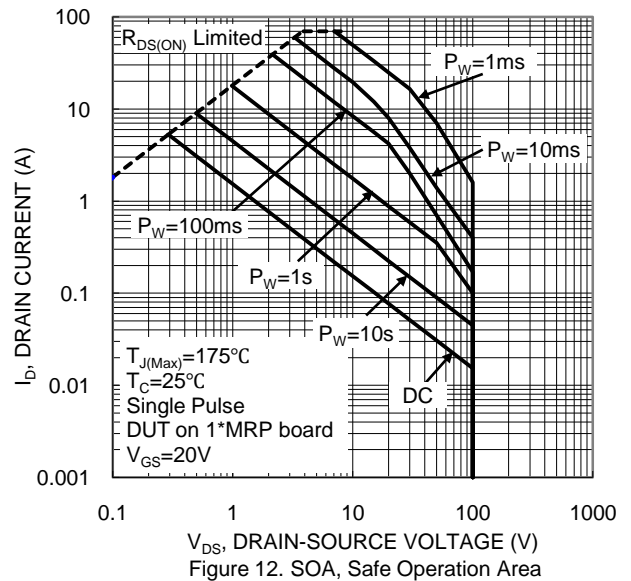


Figure 12. SOA, Safe Operation Area

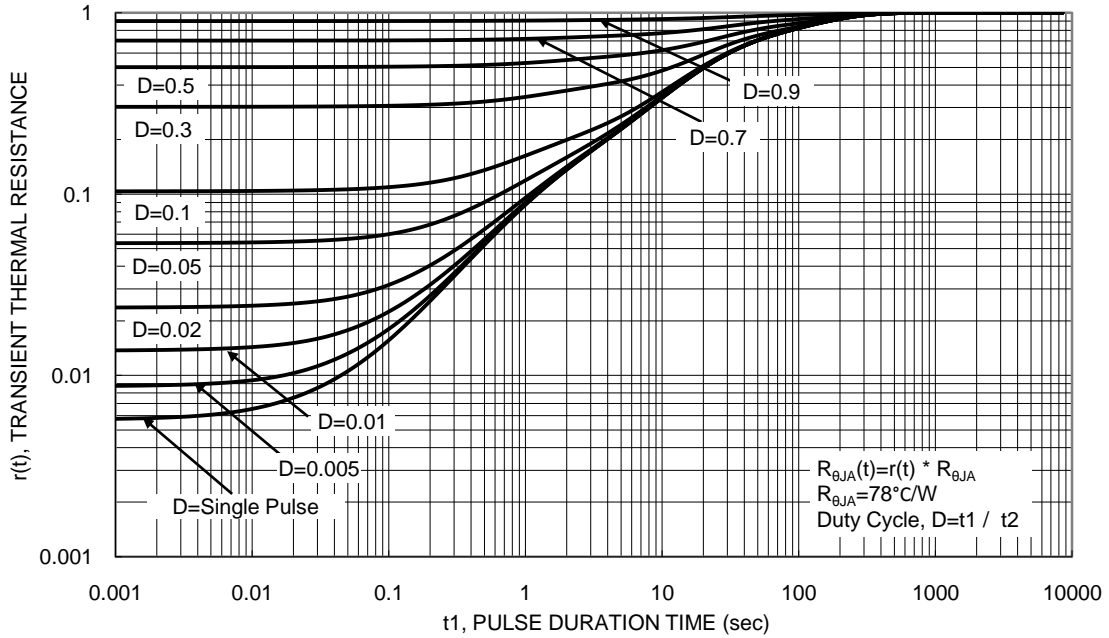
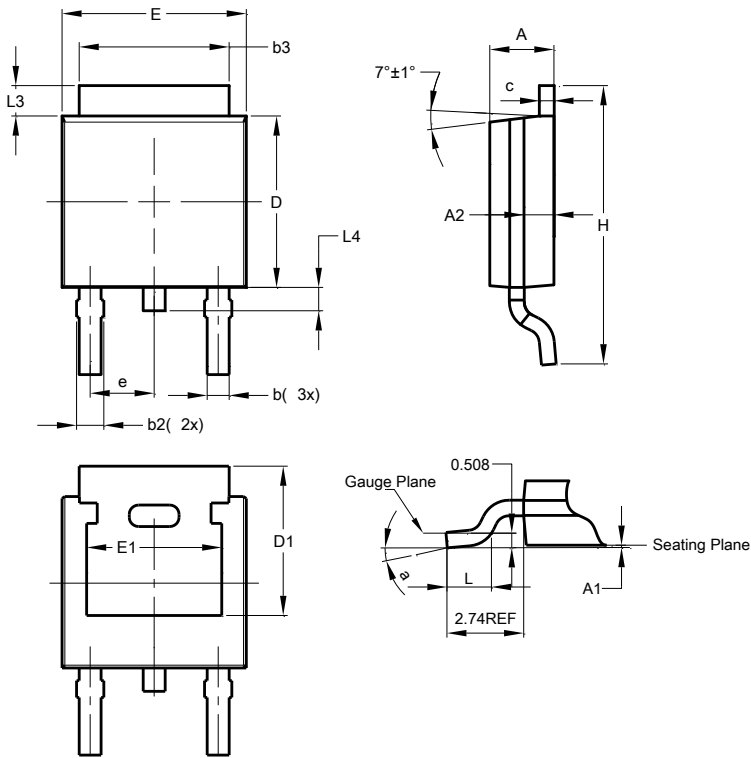


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

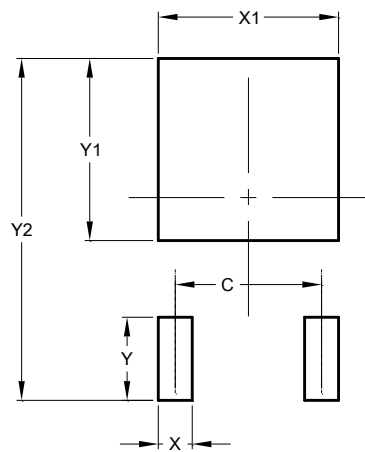


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
<b>All Dimensions in mm</b>			

NEW PRODUCT

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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